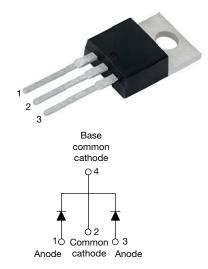
# VS-HFA08TA60C-M3

Vishay Semiconductors

### HEXFRED<sup>®</sup>, Ultrafast Soft Recovery Diode, 2 x 4 A



www.vishay.com

PRIMARY CHARACTERISTICS					
I <sub>F(AV)</sub>	2 x 4 A				
V <sub>R</sub>	600 V				
V <sub>F</sub> at I <sub>F</sub>	1.4 V				
t <sub>rr</sub> typ.	17 ns				
Package	TO-220AB 3L				
T <sub>J</sub> max.	150 °C				
Circuit configuration	Common cathode				

### FEATURES

- Ultrafast and ultrasoft recovery
- Very low I<sub>RRM</sub> and Q<sub>rr</sub>
- $\bullet$  Designed and qualified according JEDEC  $^{\textcircled{B}}\text{-}JESD47$



HALOGEN

to

 Material categorization: for definitions of compliance please see www.vishay.com/doc?99912

#### BENEFITS

- Reduced RFI and EMI
- Reduced power loss in diode and switching transistor
- Higher frequency operation
- Reduced snubbing
- · Reduced parts count

### DESCRIPTION

VS-HFA08TA60C... is a state of the art center tap ultrafast recovery diode. Employing the latest in epitaxial construction and advanced processing techniques it features a superb combination of characteristics which result in performance which is unsurpassed by any rectifier previously available. With basic ratings of 600 V and 4 A per leg continuous current, the VS-HFA08TA60C... is especially well suited for use as the companion diode for IGBTs and MOSFETs. In addition to ultrafast recovery time, the HEXFRED® product line features extremely low values of peak recovery current (I<sub>RRM</sub>) and does not exhibit any tendency to "snap-off" during the t<sub>b</sub> portion of recovery. The HEXFRED features combine to offer designers a rectifier with lower noise and significantly lower switching losses in both the diode and the switching transistor. These HEXFRED advantages can help to significantly reduce snubbing, component count and heatsink sizes. The HEXFRED VS-HFA08TA60C... is ideally suited for applications in power supplies and power conversion systems (such as inverters), motor drives, and many other similar applications where high speed, high efficiency is needed.

ABSOLUTE MAXIMUM RATINGS						
PARAMETER	SYMBOL	TEST CONDITIONS	VALUES	UNITS		
Cathode to anode voltage	V <sub>R</sub>		600	V		
Maximum continuous forward currentper leg	I_	T <sub>C</sub> = 100 °C	4			
per device	I <sub>F</sub>	$1_{\rm C} = 100$ C	8	А		
Single pulse forward current	I <sub>FSM</sub>		25	A		
Maximum repetitive forward current	I <sub>FRM</sub>		16			
Maximum newar discinction		T <sub>C</sub> = 25 °C	25	W		
Maximum power dissipation	PD	T <sub>C</sub> = 100 °C	10	vv		
Operating junction and storage temperature range	T <sub>J</sub> , T <sub>Stg</sub>		-55 to +150	°C		

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VS-HFA08TA60C-M3



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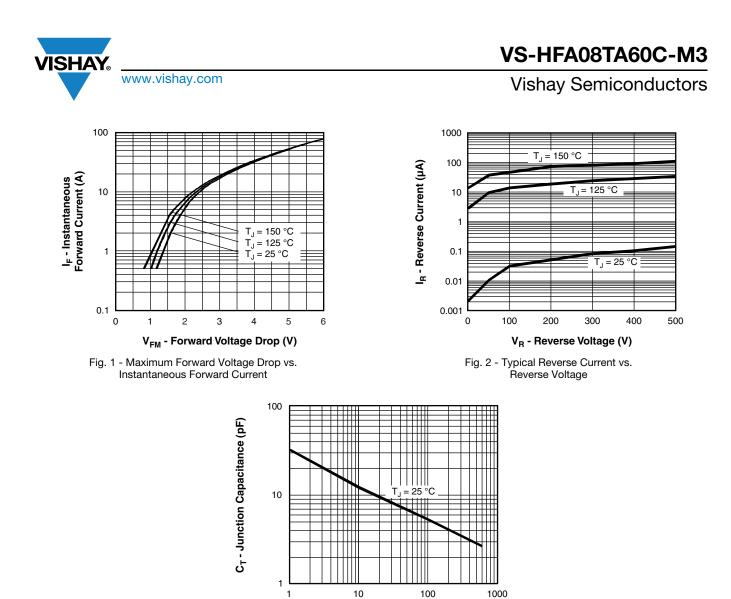
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ELECTRICAL SPECIFICATIONS (T <sub>J</sub> = 25 °C unless otherwise specified)							
PARAMETER	SYMBOL	TEST CONDITIONS		MIN.	TYP.	MAX.	UNITS
Cathode to anode breakdown voltage	V <sub>BR</sub>	I <sub>R</sub> = 100 μA		600	-	-	
Maximum forward voltage		I <sub>F</sub> = 4.0 A	See fig. 1	-	1.5	1.8	V
	V <sub>FM</sub>	I <sub>F</sub> = 8.0 A		-	1.8	2.2	
		I <sub>F</sub> = 4.0 A, T <sub>J</sub> = 125 °C		-	1.4	1.7	
Maximum reverse	la.	$V_{R} = V_{R}$ rated	See fig. 2	-	0.17	3.0	
leakage current	I <sub>RM</sub>	$T_J$ = 125 °C, $V_R$ = 0.8 x $V_R$ rated	See fig. 2	-	44	300	μA
Junction capacitance	CT	V <sub>R</sub> = 200 V	See fig. 3	-	4.0	8.0	pF
Series inductance	L <sub>S</sub>	Measured lead to lead 5 mm from p	ackage body	-	8.0	-	nH

<b>DYNAMIC RECOVERY CHARACTERISTICS</b> (T <sub>J</sub> = 25 °C unless otherwise specified)								
PARAMETER	SYMBOL	TEST CO	NDITIONS	MIN.	TYP.	MAX.	UNITS	
	t <sub>rr</sub>	$I_F = 1.0 \text{ A},  dI_F/dt = 200$	A/µs, V <sub>R</sub> = 30 V	-	17	-		
Reverse recovery time See fig. 5, 6 and 16	t <sub>rr1</sub>	T <sub>J</sub> = 25 °C		-	28	42	ns	
	t <sub>rr2</sub>	T <sub>J</sub> = 125 °C		-	38	57		
Peak recovery current	I <sub>RRM1</sub>	T <sub>J</sub> = 25 °C	I <sub>F</sub> = 4.0 A dI <sub>F</sub> /dt = 200 A/μs V <sub>R</sub> = 200 V	-	2.9	5.2	А	
See fig. 7 and 8	I <sub>RRM2</sub>	T <sub>J</sub> = 125 °C		-	3.7	6.7	~	
Reverse recovery charge	Q <sub>rr1</sub>	T <sub>J</sub> = 25 °C		-	40	60	nC	
See fig. 9 and 10	Q <sub>rr2</sub>	T <sub>J</sub> = 125 °C		-	70	105	no	
Peak rate of fall of recovery current during t <sub>b</sub> See fig. 11 and 12	dl <sub>(rec)M</sub> /dt1	T <sub>J</sub> = 25 °C		-	280	-		
	dl <sub>(rec)M</sub> /dt2	T <sub>J</sub> = 125 °C		-	235	-	A∕µs	

THERMAL - MECHANICAL SPECIFICATIONS							
PARAMETER	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNITS	
Lead temperature	T <sub>lead</sub>	0.063" from case (1.6 mm) for 10 s	-	-	300	°C	
Thermal resistance, junction to case	R <sub>thJC</sub>		-	-	5.0		
Thermal resistance, junction to ambient	R <sub>thJA</sub>	Typical socket mount	-	-	80	K/W	
Thermal resistance, case to heatsink	R <sub>thCS</sub>	Mounting surface, flat, smooth and greased	-	0.5	-		
Woight			-	2.0	-	g	
Weight			-	0.07	-	oz.	
Mounting torque			6.0 (5.0)	-	12 (10)	kgf · cm (lbf · in)	
Marking device		Case style 3L TO-220AB		HFA08TA60C			

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V<sub>R</sub> - Reverse Voltage (V)

Fig. 3 - Typical Junction Capacitance vs. Reverse Voltage

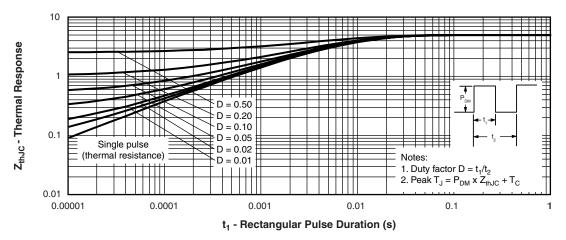


Fig. 4 - Maximum Thermal Impedance ZthJC Characteristics

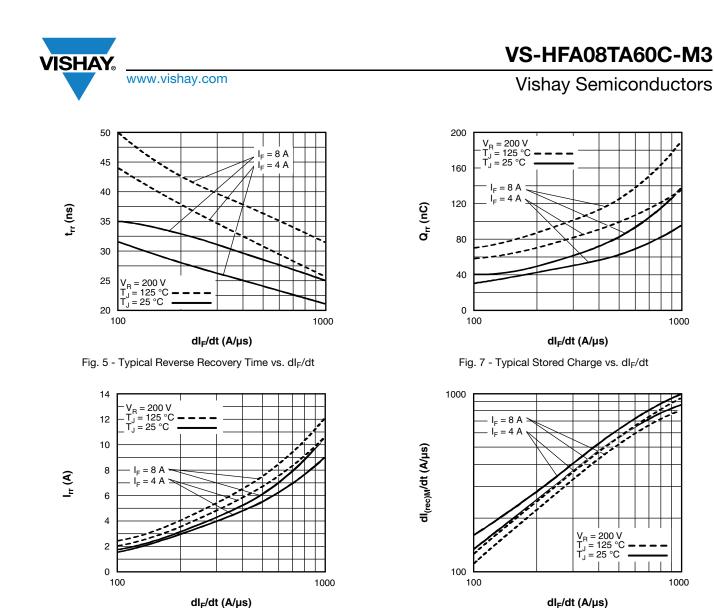


Fig. 6 - Typical Recovery Current vs. dI<sub>F</sub>/dt



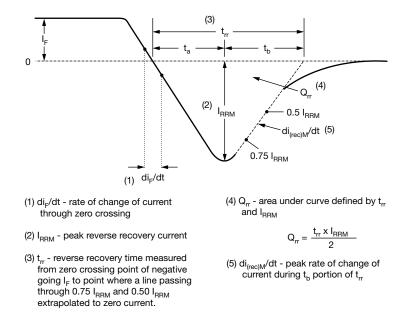


Fig. 9 - Reverse Recovery Waveform and Definitions

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#### **ORDERING INFORMATION TABLE**

Device code	VS-	HF	Α	08	ТА	60	С	-МЗ
		(2)	(3)	(4)	(5)	(6)	(7)	(8)
	1 -	Visł	nay Sem	niconduc	ctors pro	oduct		
	2 -	HEX	(FRED®	family				
	3 -	Elec	ctron irra	adiated				
	4 -	Cur	rent rati	ng (08 =	= 8 A)			
	5 -	Pac	kage:					
		TA	= 3L TO	-220AB				
	6 -	Volt	age rati	ng (60 =	= 600 V)			
	7 -	Circ	uit conf	iguratio	n:			
		C =	commo	on cathc	ode			
	7 -			ntal digit			_	
		-M3	i = halog	gen-free	, RoHS	-compli	ant, and	d termin

ORDERING INFORMATION (Example)					
PREFERRED P/N	BASE QUANTITY	PACKAGING DESCRIPTION			
VS-HFA08TA60C-M3	50	Antistatic plastic tube			

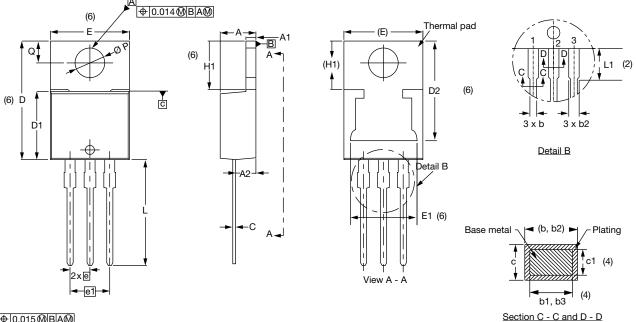
LINKS TO RELATED DOCUMENTS				
Dimensions	www.vishay.com/doc?96154			
Part marking information	www.vishay.com/doc?95028			



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## **TO-220AB 3L**

#### **DIMENSIONS** in millimeters and inches



#### ⊕0.015@BA@



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SYMBOL	MILLIN	IETERS	INC	HES	NOTES
STWDOL	MIN.	MAX.	MIN.	MAX.	NOTES
А	4.25	4.65	0.167	0.183	
A1	1.14	1.40	0.045	0.055	
A2	2.50	2.92	0.098	0.115	
b	0.69	1.01	0.027	0.040	
b1	0.38	0.97	0.015	0.038	4
b2	1.20	1.73	0.047	0.068	
b3	1.14	1.73	0.045	0.068	4
С	0.36	0.61	0.014	0.024	
c1	0.36	0.56	0.014	0.022	4
D	14.85	15.35	0.585	0.604	3
D1	8.38	9.02	0.330	0.355	

SYMBOL		IEIERƏ		пеэ	NOTES
STMBOL	MIN.	MAX.	MIN.	MAX.	NOTES
D2	11.68	13.30	0.460	0.524	6, 7
E	10.11	10.51	0.398	0.414	3, 6
E1	6.86	8.89	0.270	0.350	6
е	2.41	2.67	0.095	0.105	
e1	4.88	5.28	0.192	0.208	
H1	6.09	6.48	0.240	0.255	6
L	13.52	14.02	0.532	0.552	
L1	3.32	3.82	0.131	0.150	2
ØP	3.54	3.91	0.139	0.154	
Q	2.60	3.00	0.102	0.118	

INCHES

#### Notes

<sup>(2)</sup> Lead dimension and finish uncontrolled in L1

<sup>(4)</sup> Dimension b1, b3, and c1 apply to base metal only

<sup>(5)</sup> Controlling dimensions: inches

- (6) Thermal pad contour optional within dimensions E, H1, D2, and E1
- <sup>(7)</sup> Outline conforms to JEDEC<sup>®</sup> TO-220, except D2

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Conforms to JEDEC<sup>®</sup> outline TO-220AB

MILLIMETEDS

 $<sup>^{(1)}\,</sup>$  Dimensioning and tolerancing as per ASME Y14.5M-1994

<sup>&</sup>lt;sup>(3)</sup> Dimension D, D1, and E do not include mold flash. Mold flash shall not exceed 0.127 mm (0.005") per side. These dimensions are measured at the outermost extremes of the plastic body



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